Preferred Device

High Voltage PNP Silicon Power Transistors

Designed for line operated audio output amplifier, $SWITCHMODE^{\mathsf{TM}}$ power supply drivers and other switching applications.

Features

- 350 V (Min) V_{CEO(SUS)}
- 1.0 A Rated Collector Current
- PNP Complements to the MJD47 thru MJD50 Series
- Epoxy Meets UL 94 V-0 @ 0.125 in
- ESD Ratings: Human Body Model, 3B > 8000 V
 Machine Model, C > 400 V
- Pb-Free Package is Available

MAXIMUM RATINGS

Rating	Symbol	Max	Unit
Collector-Emitter Voltage	V _{CEO}	350	Vdc
Emitter-Base Voltage	V _{EB}	5	Vdc
Collector Current – Continuous – Peak	I _C	1.0 3.0	Adc
Total Power Dissipation @ T _C = 25°C Derate above 25°C	P _D	15 0.12	W W/°C
Total Power Dissipation (Note 1) @ T _A = 25°C Derate above 25°C	P _D	1.56 0.0125	W W/°C
Unclamped Inductive Load Energy (See Figure 10)	E	20	mJ
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	8.33	°C/W
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{\theta JA}$	80	°C/W
Lead Temperature for Soldering	TL	260	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

 These ratings are applicable when surface mounted on the minimum pad sizes recommended.



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SILICON POWER TRANSISTORS 1.0 AMPERE 350 VOLTS, 15 WATTS



DPAK CASE 369C STYLE 1

MARKING DIAGRAM



Y = Year WW = Work Week J5731 = Device Code G = Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping [†]
MJD5731T4	DPAK	2500/Tape & Reel
MJD5731T4G	DPAK (Pb-Free)	2500/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS		•		
Collector–Emitter Sustaining Voltage (Note 2) $(I_C = 30 \text{ mAdc}, I_B = 0)$	V _{CEO(sus)}	350	-	Vdc
Collector Cutoff Current (V _{CE} = 250 Vdc, I _B = 0)	ICEO	-	0.1	mAdc
Collector Cutoff Current (V _{CE} = 350 Vdc, V _{BE} = 0)	I _{CES}	-	0.01	mAdc
Emitter Cutoff Current $(V_{BE} = 5.0 \text{ Vdc}, I_{C} = 0)$	I _{EBO}	-	0.5	mAdc
ON CHARACTERISTICS (Note 2)		•		
DC Current Gain (I _C = 0.3 Adc, V _{CE} = 10 Vdc) (I _C = 1.0 Adc, V _{CE} = 10 Vdc)	h _{FE}	30 10	175 -	-
Collector–Emitter Saturation Voltage (I _C = 1.0 Adc, I _B = 0.2 Adc)	V _{CE(sat)}	-	1.0	Vdc
Base–Emitter On Voltage (I _C = 1.0 Adc, V _{CE} = 10 Vdc)	V _{BE(on)}	-	1.5	Vdc
DYNAMIC CHARACTERISTICS	•			
Current Gain – Bandwidth Product (I _C = 0.2 Adc, V _{CE} = 10 Vdc, f = 2.0 MHz)	f⊤	10	-	MHz
Small–Signal Current Gain (I _C = 0.2 Adc, V _{CE} = 10 Vdc, f = 1.0 kHz)	h _{fe}	25	-	_

^{2.} Pulse Test: Pulse Width \leq 300 $\mu s,$ Duty Cycle \leq 2.0%.

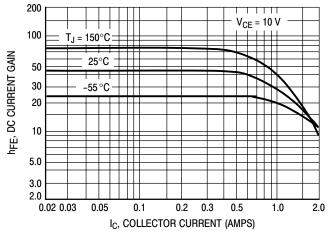


Figure 1. DC Current Gain

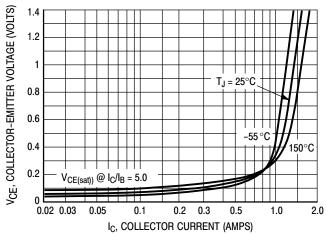


Figure 2. Collector-Emitter Saturation Voltage

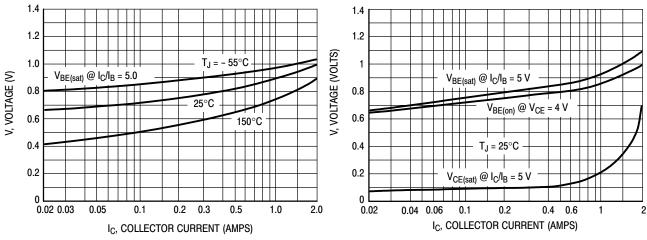


Figure 3. Base-Emitter Voltage

Figure 4. "On" Voltages

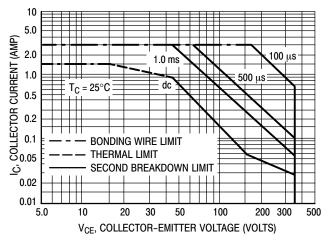


Figure 5. Forward Bias Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 5 is based on $T_{J(pk)} = 150^{\circ}C$; T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \le 150^{\circ}C$. $T_{J(pk)}$ may be calculated from the data in Figure 6. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

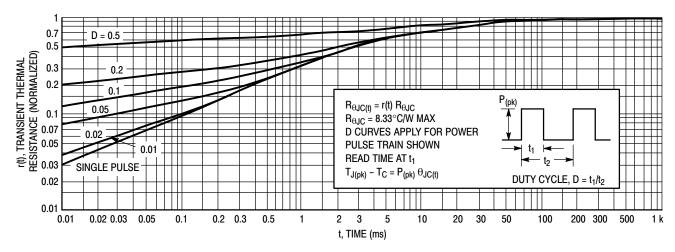


Figure 6. Thermal Response

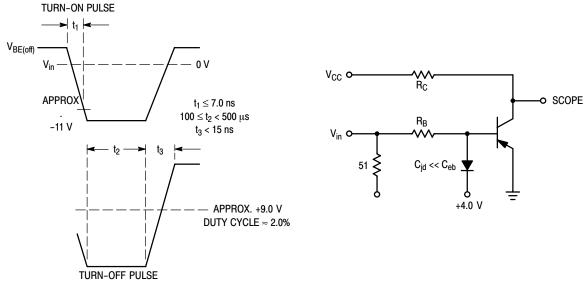


Figure 7. Switching Time Equivalent Circuit

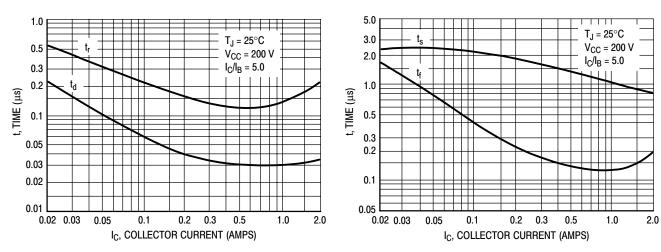


Figure 8. Turn-On Resistive Switching Times

Figure 9. Resistive Turn-Off Switching Times

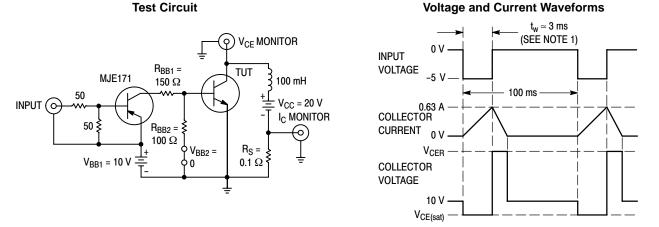
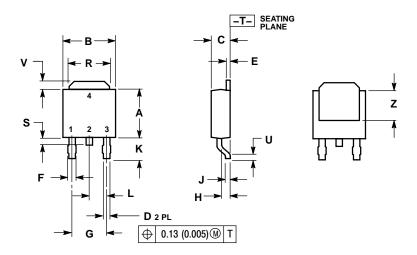


Figure 10. Inductive Load Switching

PACKAGE DIMENSIONS

DPAK CASE 369C **ISSUE O**



NOTES

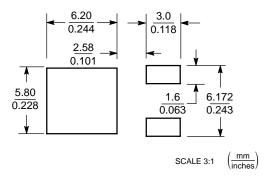
- 1. DIMENSIONING AND TOLERANCING
- PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.235	0.245	5.97	6.22
В	0.250	0.265	6.35	6.73
С	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
Е	0.018	0.023	0.46	0.58
F	0.037	0.045	0.94	1.14
G	0.180	0.180 BSC		BSC
Н	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.102	0.114	2.60	2.89
L	0.090	BSC	2.29	BSC
R	0.180	0.215	4.57	5.45
S	0.025	0.040	0.63	1.01
U	0.020		0.51	
٧	0.035	0.050	0.89	1.27
Z	0.155		3.93	

STYLE 1:

- PIN 1. BASE
 2. COLLECTOR
 3. EMITTER
 4. COLLECTOR

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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